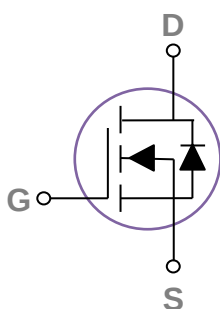
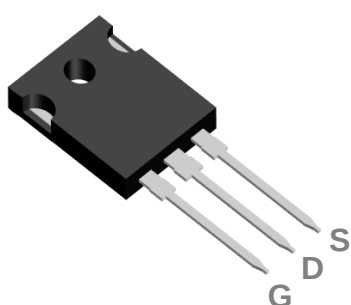


General Description

These N-Channel enhancement mode power field effect transistors are using super junction MOS technology.

This advanced technology has been especially tailored to minimize on-state resistance, provide superior switching performance, and withstand high energy pulse in the avalanche and commutation mode. These devices are well suited for high efficiency fast switching applications.

TO247 Pin Configuration



BVDSS	RDS(ON)	ID
600V	50mΩ	55A

Features

- 600V, 55A, $R_{DS(ON)} = 50\text{m}\Omega$ @ $V_{GS} = 10\text{V}$
- Improved dv/dt capability
- Fast switching
- Green Device Available

Applications

- PFC Power Supply Stages
- Motor Control
- DC-DC Converters
- Adapter

Absolute Maximum Ratings $T_c=25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	600	V
V_{GS}	Gate-Source Voltage	± 30	V
I_D	Drain Current – Continuous ($T_c=25^\circ\text{C}$)	55	A
	Drain Current – Continuous ($T_c=100^\circ\text{C}$)	35	A
I_{DM}	Drain Current – Pulsed ¹	220	A
EAS	Single Pulse Avalanche Energy	1535	mJ
P_D	Power Dissipation ($T_c=25^\circ\text{C}$)	208	W
	Power Dissipation – Derate above 25°C	1.67	W/ $^\circ\text{C}$
T_{STG}	Storage Temperature Range	-55 to 150	$^\circ\text{C}$
T_J	Operating Junction Temperature Range	-55 to 150	$^\circ\text{C}$

Thermal Characteristics

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JA}$	Thermal Resistance Junction to ambient	---	62	$^\circ\text{C/W}$
$R_{\theta JC}$	Thermal Resistance Junction to Case	---	0.6	$^\circ\text{C/W}$

Electrical Characteristics (T_J=25 °C, unless otherwise noted)
Off Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _D =250μA	600	---	---	V
I _{DSS}	Drain-Source Leakage Current	V _{DS} =600V, V _{GS} =0V, T _J =25°C	---	---	1	μA
		V _{DS} =480V, V _{GS} =0V, T _J =125°C	---	---	10	μA
I _{GSS}	Gate-Source Leakage Current	V _{GS} =±30V, V _{DS} =0V	---	---	±100	nA

On Characteristics

R _{DS(ON)}	Static Drain-Source On-Resistance	V _{GS} =10V, I _D =10A	---	40	50	mΩ
V _{GS(th)}	Gate Threshold Voltage	V _{GS} =V _{DS} , I _D =250μA	3	---	5	V

Dynamic and switching Characteristics

Q _g	Total Gate Charge ^{2, 3}	V _{DS} =480V, V _{GS} =10V, I _D =30A	---	86	170	nC
Q _{gs}	Gate-Source Charge ^{2, 3}		---	18.5	35	
Q _{gd}	Gate-Drain Charge ^{2, 3}		---	23	45	
T _{d(on)}	Turn-On Delay Time ^{2, 3}	V _{DS} =480V, V _{GS} =10V, R _G =25Ω I _D =30A	---	70	140	ns
T _r	Rise Time ^{2, 3}		---	56	110	
T _{d(off)}	Turn-Off Delay Time ^{2, 3}		---	155	300	
T _f	Fall Time ^{2, 3}		---	80	160	
C _{iss}	Input Capacitance	V _{DS} =100V, V _{GS} =0V, F=1MHz	---	4620	9300	pF
C _{oss}	Output Capacitance		---	145	300	
C _{rss}	Reverse Transfer Capacitance		---	3.2	7	
R _g	Total Gate Charge	V _{GS} =0V, V _{DS} =0V, F=1MHz	---	3.6	---	Ω

Drain-Source Diode Characteristics and Maximum Ratings

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I _S	Continuous Source Current	V _G =V _D =0V, Force Current	---	---	55	A
I _{SM}	Pulsed Source Current		---	---	110	A
V _{SD}	Diode Forward Voltage	V _{GS} =0V, I _S =25A, T _J =25°C	---	---	1.4	V
t _{rr}	Reverse Recovery Time	V _R =400V, I _S =10A	---	190	---	ns
Q _{rr}	Reverse Recovery Charge	di/dt=100A/μs, T _J =25°C	---	120	---	nC

Note :

1. Repetitive Rating : Pulsed width limited by maximum junction temperature.
2. The data tested by pulsed , pulse width ≤ 300μs , duty cycle ≤ 2%.
3. Essentially independent of operating temperature.

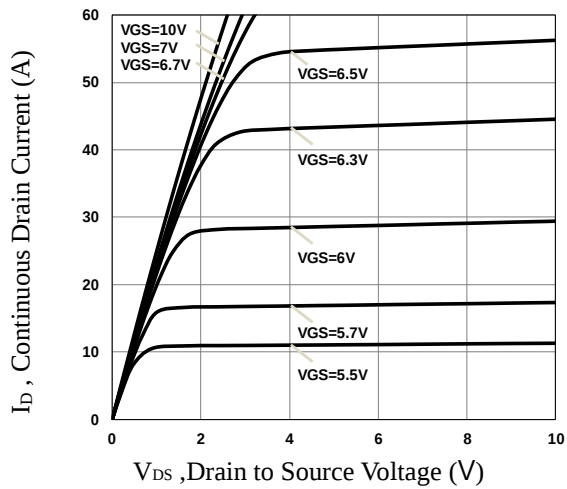


Fig.1 Typical Output Characteristics

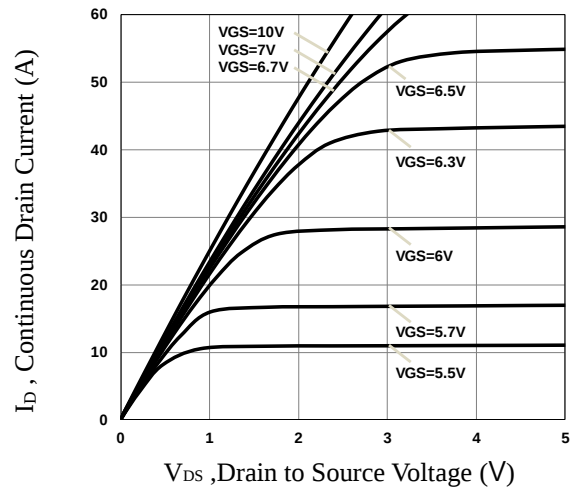


Fig.2 Typical Output Characteristics

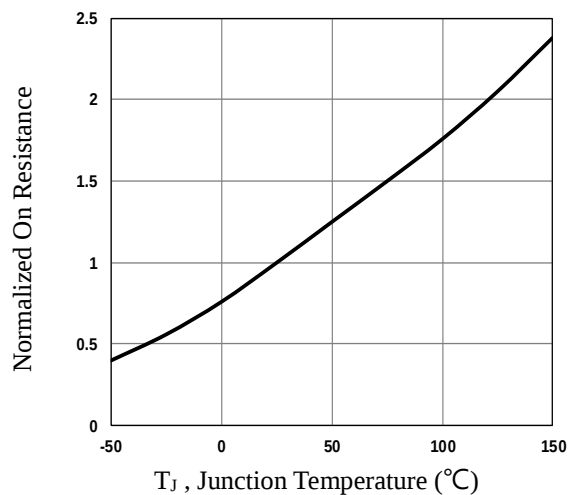


Fig.3 Normalized $R_{DS(on)}$ vs. T_J

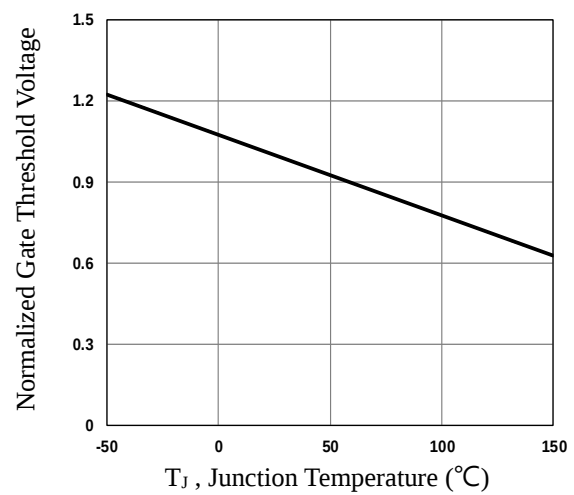


Fig.4 Normalized V_{th} vs. T_J

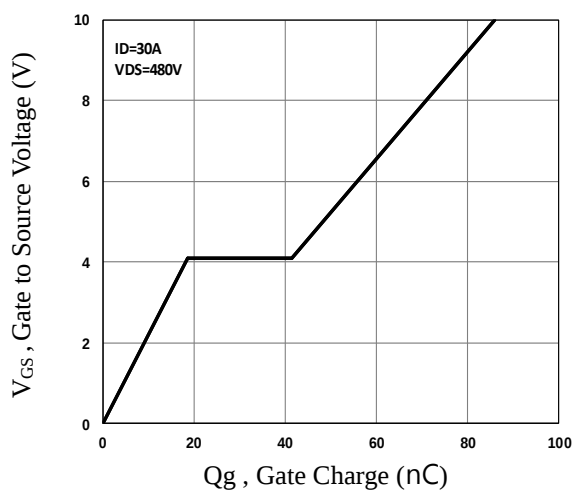


Fig.5 Gate Charge Characteristics

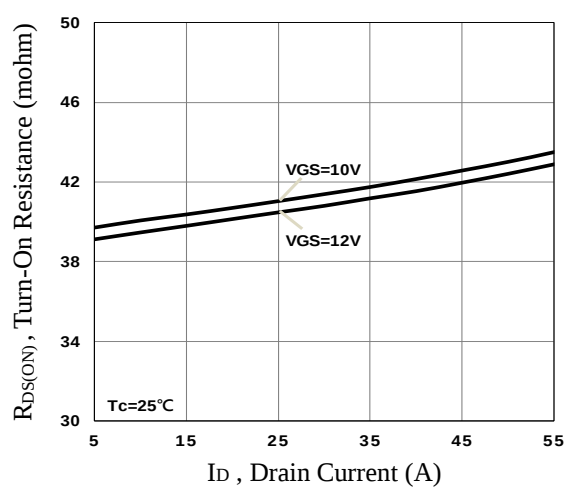
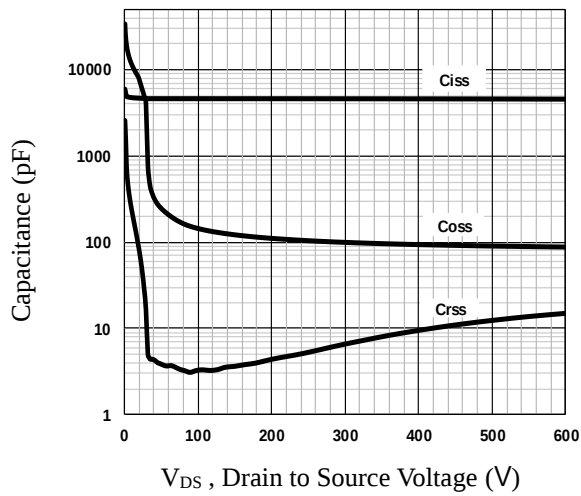
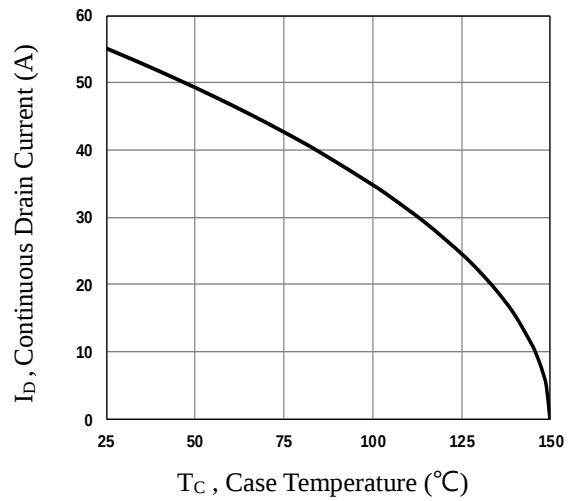
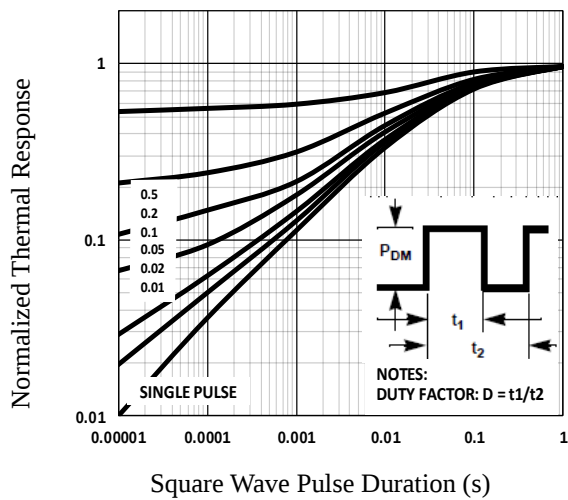
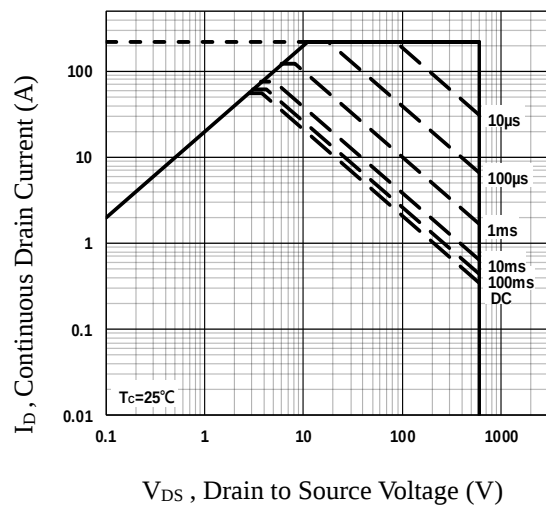
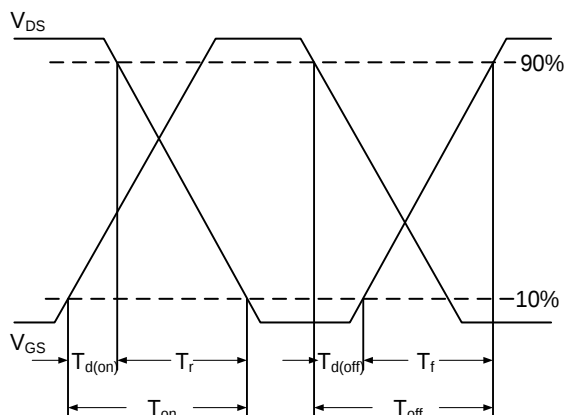
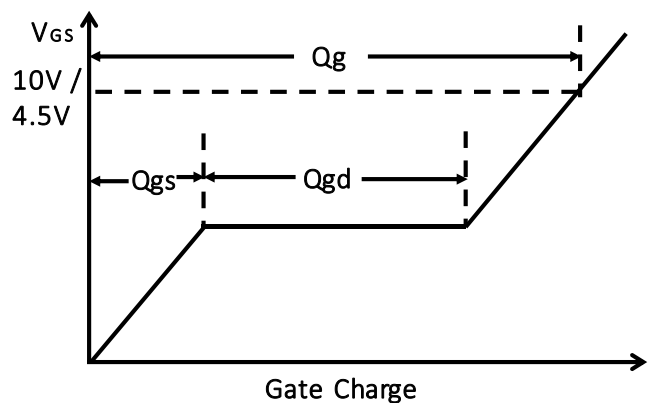
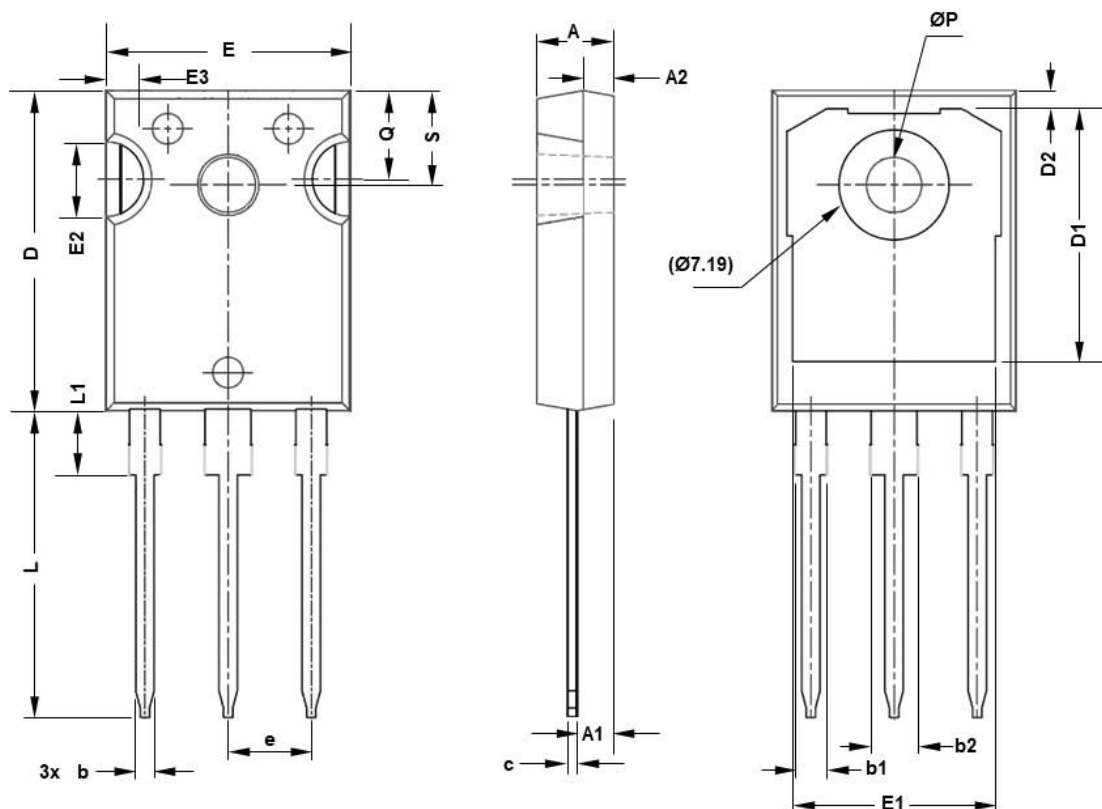


Fig.6 Turn-On Resistance vs. I_D

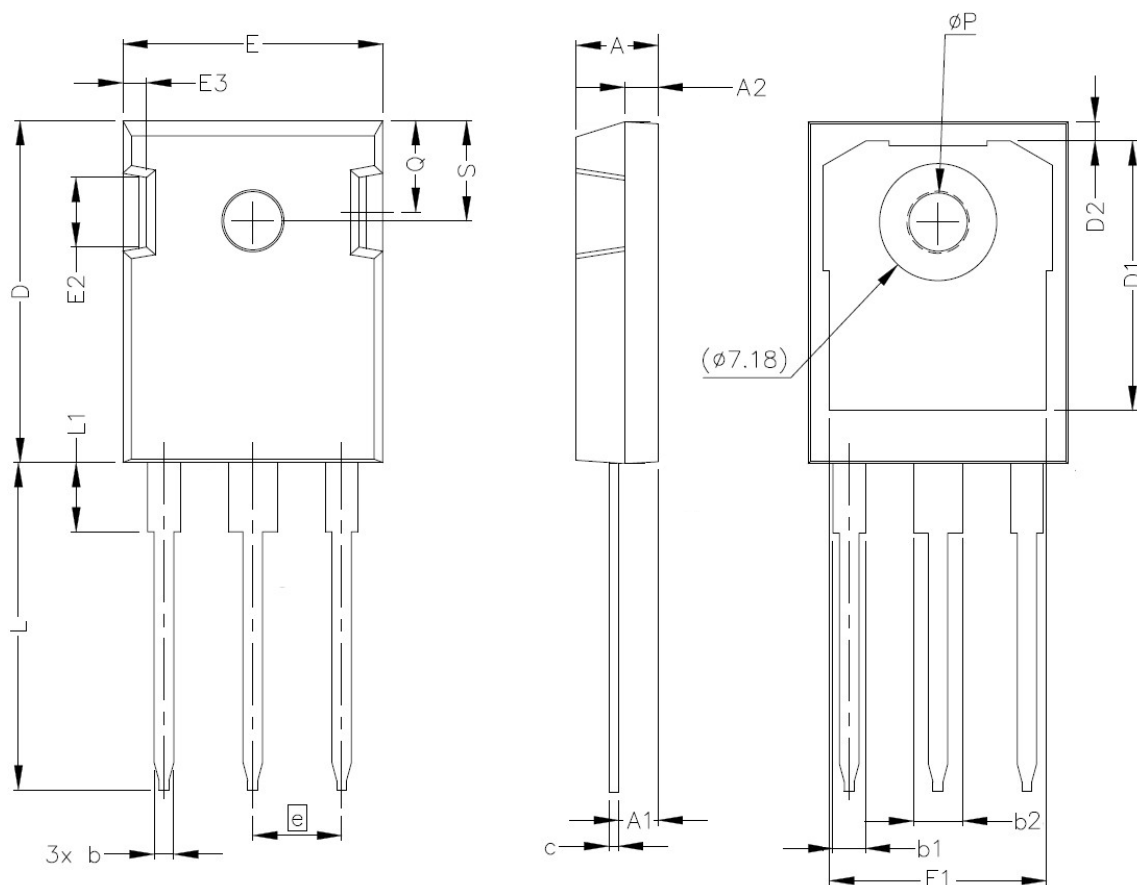

Fig.7 Capacitance Characteristics

Fig.8 Continuous Drain Current vs. T_c

Fig.9 Normalized Transient Impedance

Fig.10 Maximum Safe Operation Area

Fig.11 Switching Time Waveform

Fig.12 Gate Charge Waveform

TO247 PACKAGE INFORMATION

VERSION A



SYMBOL	mm		SYMBOL	mm	
	MIN	MAX		MIN	MAX
A	4.83	5.21	E2	4.32	5.49
A1	2.29	2.55	E3	2.15	2.80
A2	1.50	2.49	e	5.44BSC	
b	1.12	1.33	L	19.81	20.32
b1	1.91	2.39	L1	4.10	4.40
b2	2.87	3.22	ØP	3.56	3.65
C	0.55	0.69	Q	5.39	6.20
D	20.80	21.10	S	6.04	6.30
D1	16.25	17.65			
D2	0.51	1.35			
E	15.75	16.13			
E1	13.46	14.16			

VERSION B


SYMBOL	mm		SYMBOL	mm	
	MIN	MAX		MIN	MAX
A	4.75	5.25	E2	3.70	5.30
A1	2.16	2.66	E3	1.00	2.75
A2	1.75	2.25	e	5.44BSC	
b	1.07	1.35	L	19.52	20.32
b1	1.90	2.41	L1	4.10	4.40
b2	2.87	3.38	φP	3.35	3.85
c	0.50	0.70	Q	5.40	6.20
D	20.60	21.40	S	6.15BSC	
D1	16.15	17.65			
D2	0.95	1.35			
E	15.50	16.10			
E1	12.40	13.60			